

FIG. 1

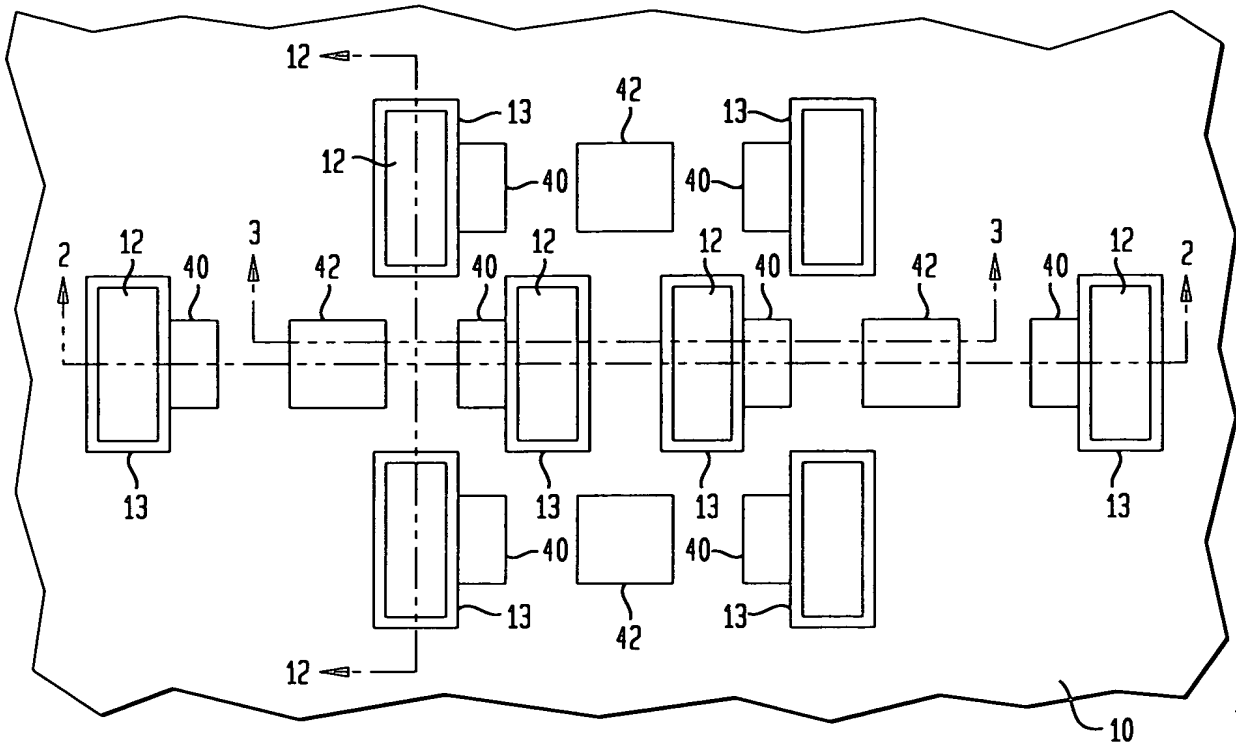
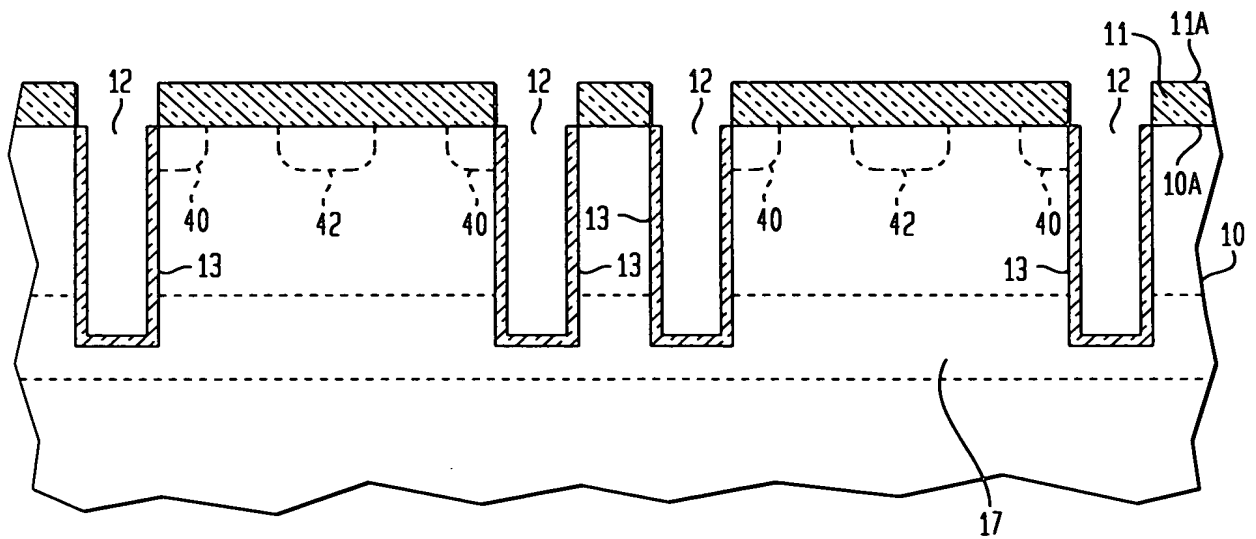


FIG. 2



This cross-sectional view shows a semiconductor device with a substrate 10. A trench 13 is formed in the substrate, with a bottom surface 17. A gate structure 14 is formed on the side walls of the trench. A conductive layer 15 is formed on the bottom surface of the trench. A conductive layer 16 is formed on the top surface of the substrate. A conductive layer 11 is formed on the top surface of the substrate. A conductive layer 10A is formed on the top surface of the substrate. A conductive layer 40 is formed on the top surface of the substrate. A conductive layer 42 is formed on the top surface of the substrate.

FIG. 4

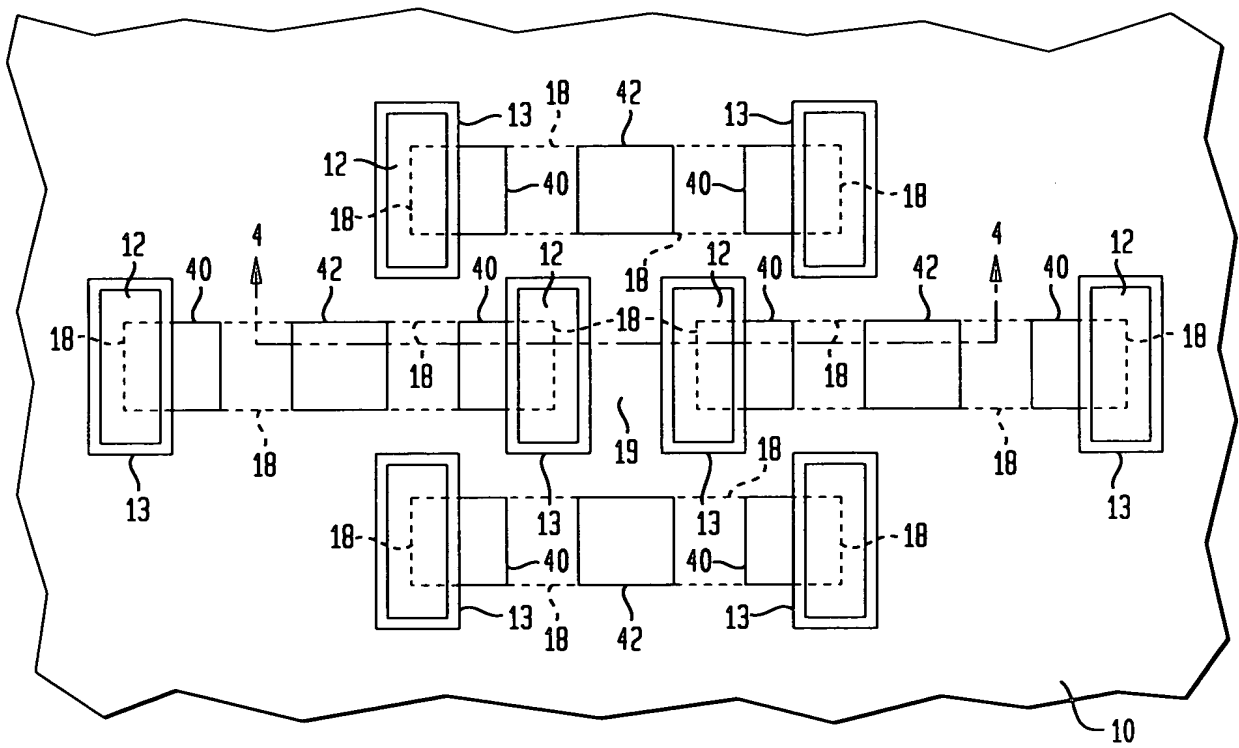


FIG. 7

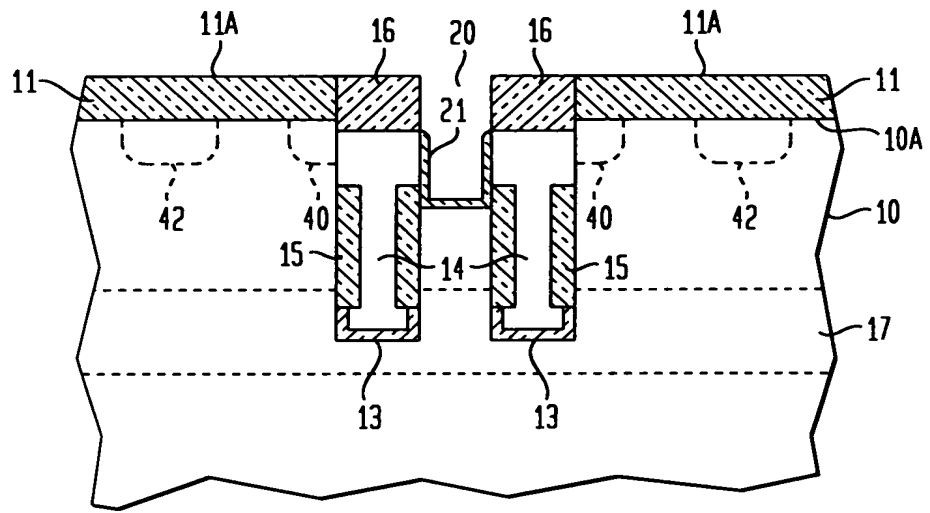


FIG. 8

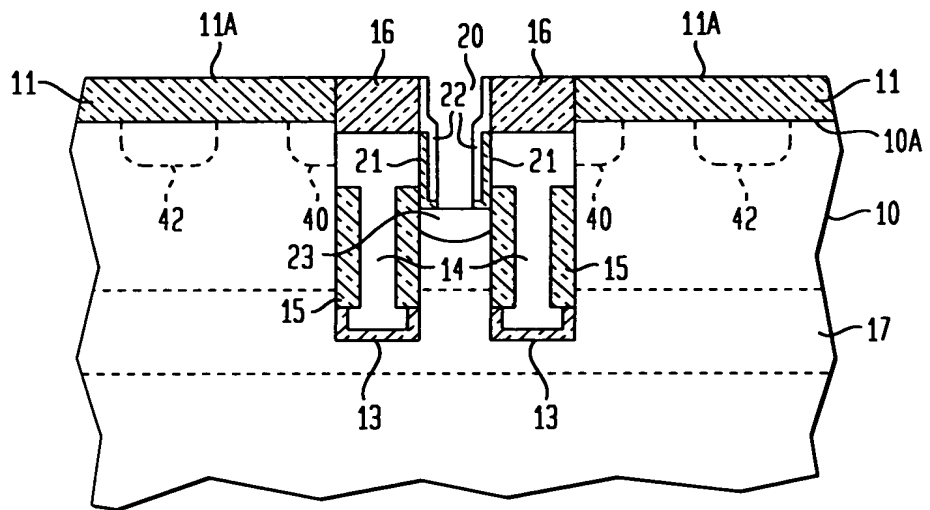


FIG. 9

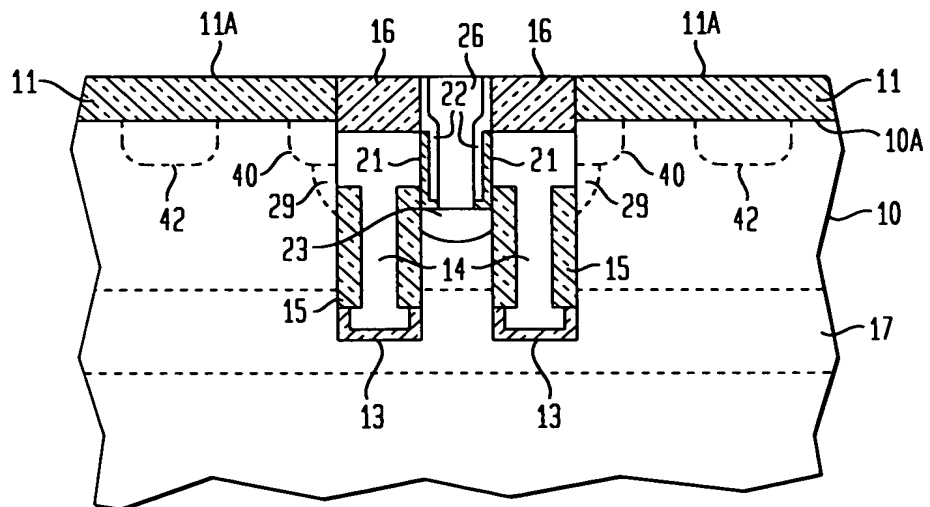


FIG. 10

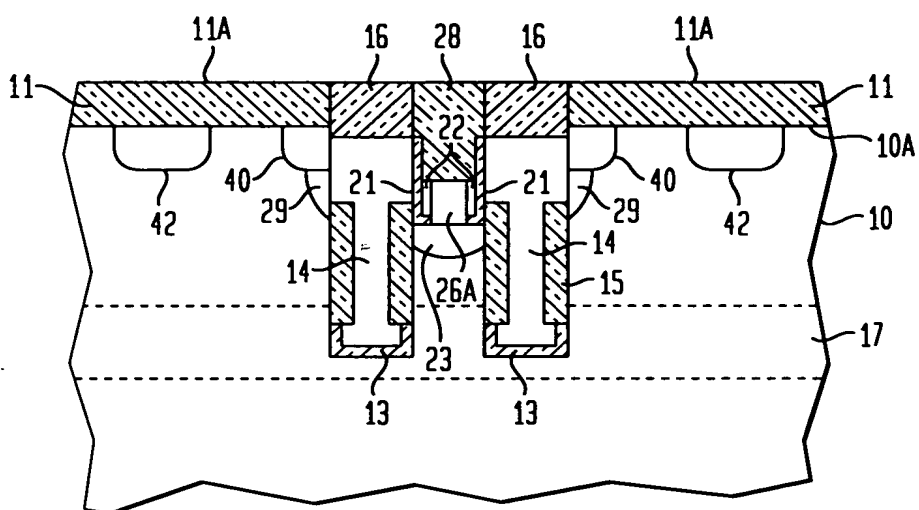


FIG. 11

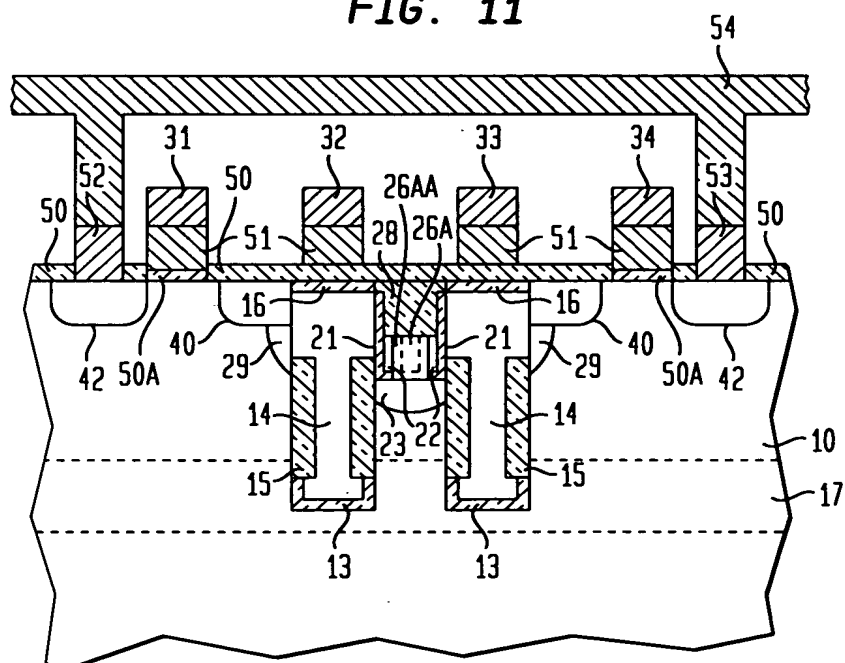


FIG. 12

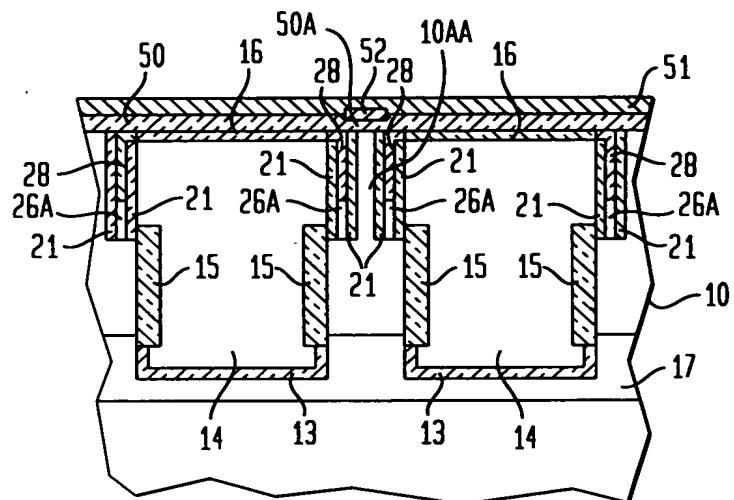


FIG. 13

